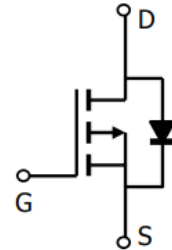


»Features

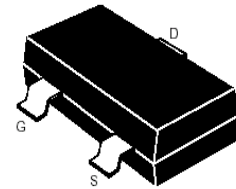
$V_{DS} = -30V$
 $I_D = -3 A$
 $R_{DS(ON)} @V_{GS} = -10V, Typ = 65m\Omega$
 $R_{DS(ON)} @V_{GS} = -4.5V, Typ = 75m\Omega$

»Pin Configurations



»General Description

- Advanced trench process technology
- High Density Cell Design For Ultra Low On-Resistance
- SOT-23 for Surface Mount Package.



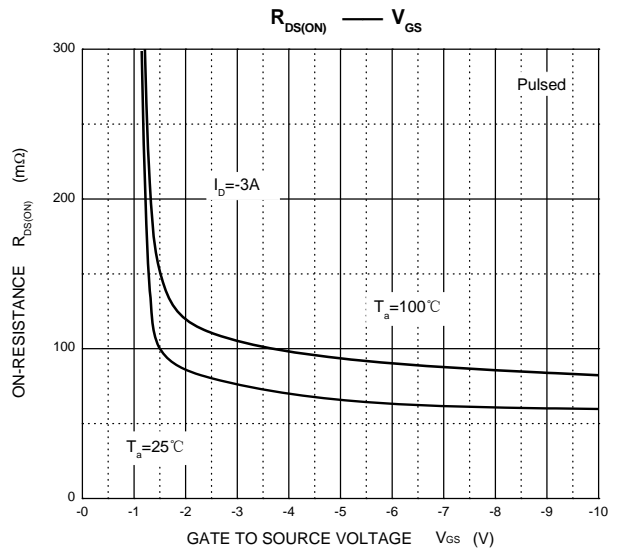
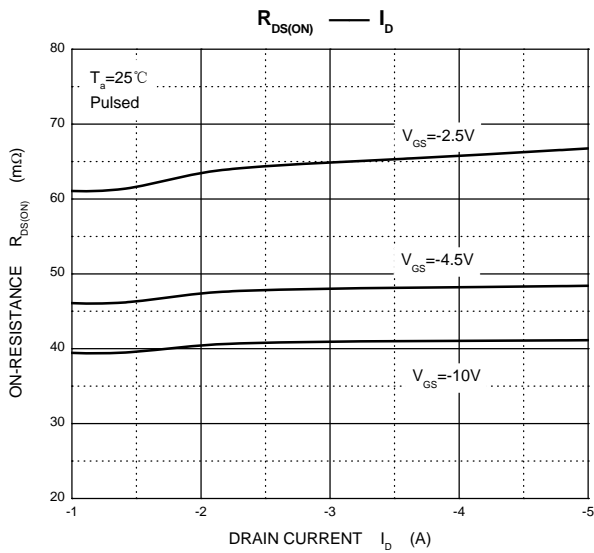
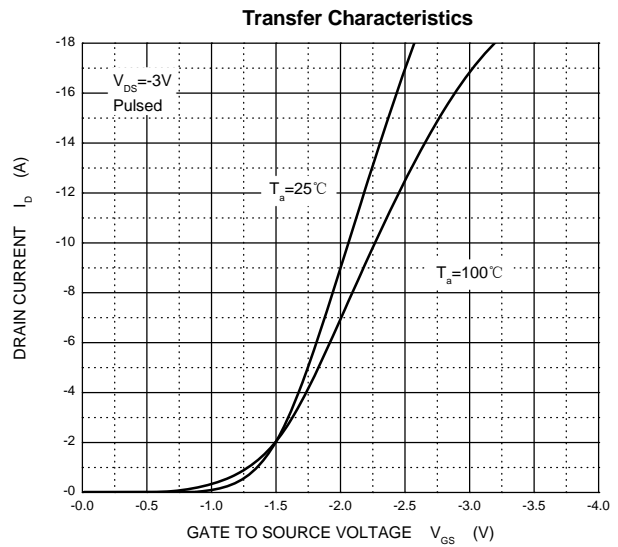
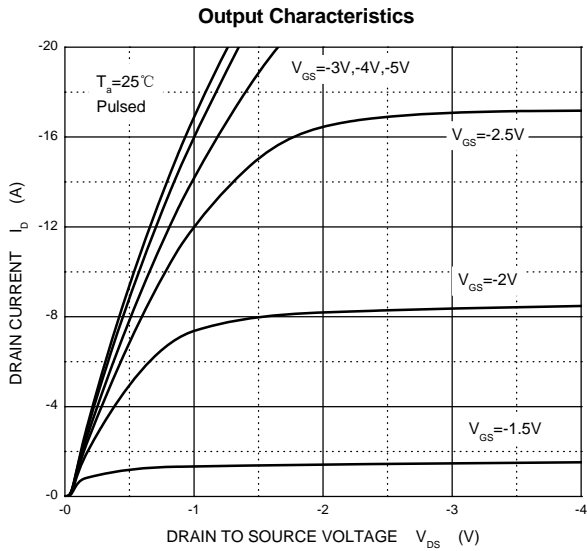
»Absolute Maximum Ratings @ $T_A=25^{\circ}C$ unless otherwise noted

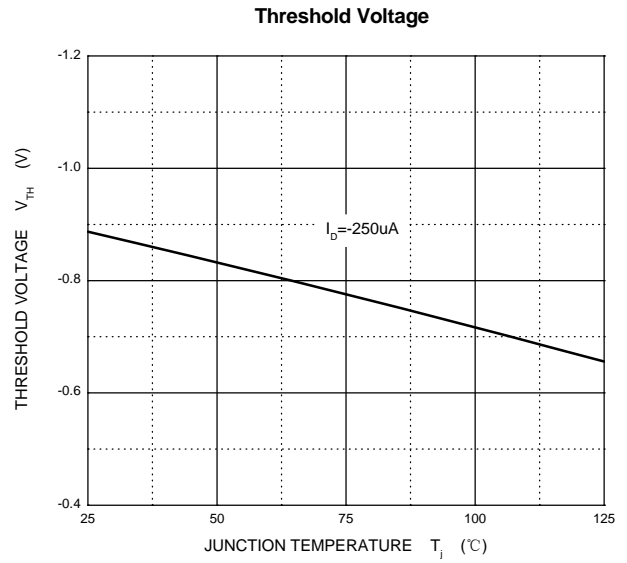
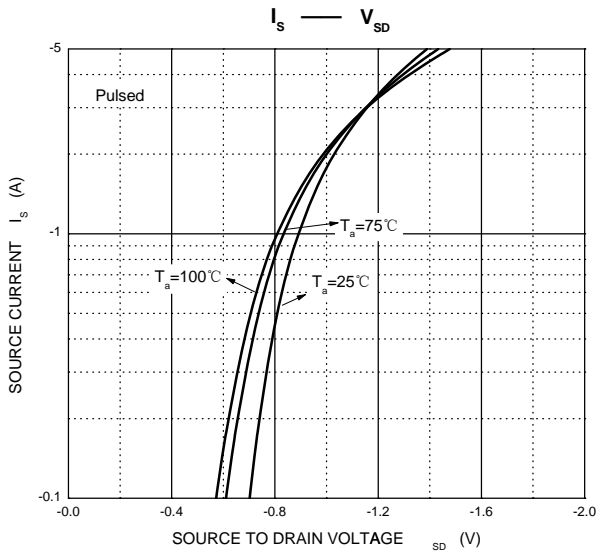
Characteristic	Symbol	Max	Unit
Drain-Source Voltage	BV_{DSS}	-30	V
Gate- Source Voltage	V_{GS}	± 12	V
Drain Current (continuous)	I_D	-3.0	A
Drain Current (pulsed)	I_{DM}	-12	A
Total Device Dissipation	P_D	1200	mW
Junction	T_J	150	$^{\circ}C$
Storage Temperature	T_{stg}	-55to+150	$^{\circ}C$

»Electrical Characteristics @ $T_A=25^{\circ}\text{C}$ unless otherwise noted

Characteristic	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage ($I_D = -250\mu\text{A}, V_{GS}=0\text{V}$)	BV_{DSS}	-30	—	—	V
Gate Threshold Voltage ($I_D = -250\mu\text{A}, V_{GS}=V_{DS}$)	$V_{GS(th)}$	-0.5	-0.8	-1.2	V
Diode Forward Voltage Drop ($I_S = -3\text{A}, V_{GS}=0\text{V}$)	V_{SD}	—	—	-1.2	V
Zero Gate Voltage Drain Current ($V_{GS}=0\text{V}, V_{DS}= -24\text{V}$)	I_{DSS}	—	—	-1	μA
Gate Body Leakage ($V_{GS}=\pm 12\text{V}, V_{DS}=0\text{V}$)	I_{GSS}	—	—	± 100	nA
Static Drain-Source On-State Resistance ($I_D = -3\text{A}, V_{GS} = -10\text{V}$)	$R_{DS(ON)}$	—	65	80	$\text{m}\Omega$
Static Drain-Source On-State Resistance ($I_D = -3\text{A}, V_{GS} = -4.5\text{V}$)	$R_{DS(ON)}$	—	75	90	$\text{m}\Omega$
Input Capacitance ($V_{GS}=0\text{V}, V_{DS}= -15\text{V}, f=1\text{MHz}$)	C_{ISS}	—	954	—	pF
Output Capacitance ($V_{GS}=0\text{V}, V_{DS}= -15\text{V}, f=1\text{MHz}$)	C_{OSS}	—	115	—	pF
Turn-ON Time ($V_{DS}= -15\text{V}, V_{GS}=-10\text{V}, R_{GEN}=6\Omega$)	$t_{(on)}$	—	6	—	ns
Turn-OFF Time ($V_{DS}= -15\text{V}, V_{GS}=-10\text{V}, R_{GEN}=6\Omega$)	$t_{(off)}$	—	38	—	ns

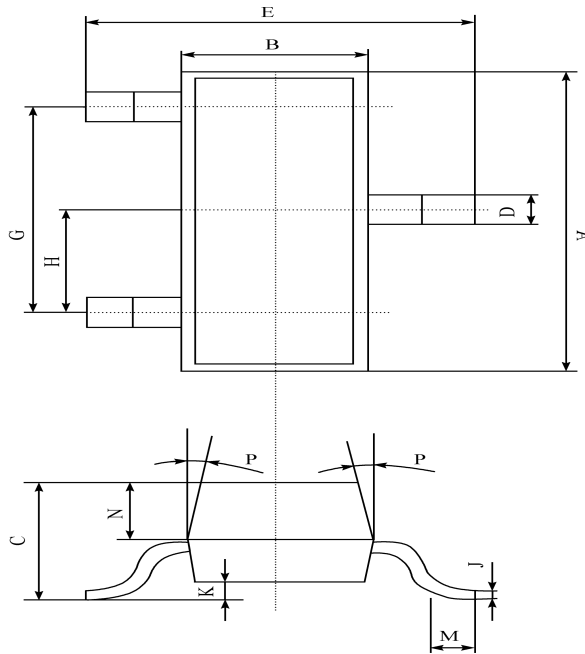
»Typical Performance Characteristics (T_J = 25 °C, unless otherwise noted)





»Package Information

SOT-23



A	2.90 ± 0.10
B	1.30 ± 0.10
C	1.00 ± 0.10
D	0.40 ± 0.10
E	2.40 ± 0.20
G	1.90 ± 0.10
H	0.95 ± 0.05
J	0.13 ± 0.05
K	0.00-0.10
M	≥ 0.2
N	0.60 ± 0.10
P	7 ± 2°

»Ordering information

Order code	Package	Marking	Base qty	Delivery mode
AO3401F	SOT-23	A19T	3K	Tape and reel

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